

General Description

The 8N50 uses advanced Manufacturing of high voltage MOSFET process , can provide excellent RDS(ON). These devices are well suited for high efficiency switched mode power supplies, active power factor correction based on half bridge topology.

Features

- Fast switching
- 100% avalanche tested
- Improved dv/dt capability

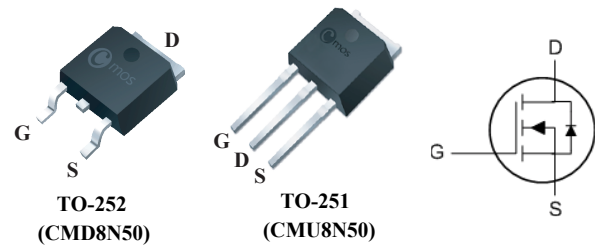
Product Summary

BVDSS	RDSON	ID
500V	0.85Ω	8A

Applications

- Adapter
- Switched Mode Power Supplies (SMPS)
- Uninterruptible Power Supply (UPS)

TO-252/251 Pin Configuration



Absolute Maximum Ratings

$T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Value	Units
V_{DSS}	Drain-Source Voltage	500	V
I_D	Drain Current - Continuous ($T_C = 25^\circ\text{C}$)	8	A
	- Continuous ($T_C = 100^\circ\text{C}$)	5	A
I_{DM}	Drain Current - Pulsed ^a	24	A
V_{GSS}	Gate-Source Voltage	± 30	V
E_{AS}	Single Pulsed Avalanche Energy ^b	64	mJ
dv/dt	Peak Diode Recovery dv/dt ^c	4.5	V/ns
P_D	Power Dissipation ($T_C = 25^\circ\text{C}$)	130	W
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150	$^\circ\text{C}$
T_L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	300	$^\circ\text{C}$

Thermal Characteristics

Symbol	Parameter	Value	Units
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case Max.	0.9	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient Max.	62.5	$^\circ\text{C}/\text{W}$

Electrical Characteristic

 $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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Off Characteristics

BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	500	--	--	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 500\text{ V}, V_{GS} = 0\text{ V}$	--	--	1	μA
		$V_{DS} = 400\text{ V}, T_C = 125^\circ\text{C}$	--	--	10	
I_{GSSF}	Gate-Body Leakage Current, Forward	$V_{GS} = 30\text{ V}, V_{DS} = 0\text{ V}$	--	--	100	nA
I_{GSSR}	Gate-Body Leakage Current, Reverse	$V_{GS} = -30\text{ V}, V_{DS} = 0\text{ V}$	--	--	-100	nA

On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	2.0	--	4.0	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 10\text{ V}, I_D = 3\text{ A}$	--	--	0.85	Ω
g_{FS}	Forward Transconductance	$V_{DS} = 10\text{ V}, I_D = 5\text{ A}$	--	10	--	S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 25\text{ V}$ $V_{GS} = 0\text{ V}$ $f = 1.0\text{ MHz}$	--	1500	--	pF
C_{oss}	Output Capacitance		--	210	--	pF
C_{rss}	Reverse Transfer Capacitance		--	80	--	pF

Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 250\text{ V}$ $I_D = 8\text{ A}$ $R_G = 25\Omega$	--	15	--	ns
t_r	Turn-On Rise Time		--	62	--	ns
$t_{d(off)}$	Turn-Off Delay Time		--	93	--	ns
t_f	Turn-Off Fall Time		--	48	--	ns
Q_g	Total Gate Charge	$V_{DS} = 400\text{ V}$ $I_D = 8\text{ A}$ $V_{GS} = 10\text{ V}$	--	26	--	nC
Q_{gs}	Gate-Source Charge		--	4	--	nC
Q_{gd}	Gate-Drain Charge		--	13	--	nC

Drain-Source Diode Characteristics and Maximum Ratings

I _S	Maximum Continuous Drain-Source Diode Forward Current		--	--	8	A
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current		--	--	24	A
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0 V, I _S = 8A	--	--	1.4	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _S = 8A dI /dt = 100 A/μs	--	340	--	ns
Q _{rr}	Reverse Recovery Charge		--	3	--	μC

Notes:

- Repetitive Rating: Pulse width limited by maximum junction temperature
- $L=0.5\text{ mH}$, $I_{AS}=16\text{ A}$, $V_{DD}=50\text{ V}$, $V_G=10\text{ V}$, Starting $T_J=25^\circ\text{C}$
- $I_{SD}\leq 8.0\text{ A}$, $dI/dt \leq 200\text{ A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$
- Pulse Test: Pulse width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$
- Essentially Independent of Operating Temperature Typical Characteristics

This product has been designed and qualified for the consumer market.

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Cmos reserves the right to improve product design, functions and reliability without notice.

